

Ge Single Crystal and Wafers

< TYPICAL SPECIFICATIONS >

General Properties	Structure :	Cubic, a = 5.6754 Å		
	Density :	5.765 g/cm ³		
	Melting Point :	937.4 °C		
	Thermal Conductivity :	640		
Crystal Growth Technology	Czochralski			
Doping available	Undoped (Natural N-type)	Sb Doping	Doping In or Ga	
Conductive Type	/	N	P	
Resistivity, Ω cm	>35	0.05	0.05 - 0.1	
EPD	<4 × 10 ³ /cm ²	<4 × 10 ³ /cm ²	<4 × 10 ³ /cm ²	
Crystal Grades and Application (please specify when you order)	Electronic Grade : Used for diodes and transistors Infrared Grade : Used for IR optical window Cell Grade : Used for substrates of solar cell			

< STANDARD SPECS >

Crystal Orientation	<111>, <100> and <110> ±0.5° Or special orientation
Crystal boule as grown	φ 1" ~ φ 5" diameter × 200 mm Length
Standard blank as cut	φ 1" × 0.5mm, φ 2" × 0.6mm
Standard Polished wafer One or two sides polished	φ 1" × 0.30 mm, φ 2" × 0.5mm

* Special size is available upon request.